

RF Amplifier, N-Channel MMBF4416A

Features

- This Device is Designed for RF Amplifiers
- Sourced from Process 50
- This is a Pb-Free and Halide Free Device

ABSOLUTE MAXIMUM RATINGS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted.})$ (Notes 1, 2)

Symbol	Parameter	Value	Unit	
V_{DG}	Drain-Gate Voltage	35	V	
V_{GS}	Gate-Source Voltage	-35	V	
I_{GF}	Forward Gate Current	10	mA	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

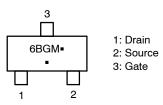
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. **onsemi** should be consulted on applications involving pulsed or low-duty-cycle operations.



SOT-23 CASE 318BM

MARKING DIAGRAM



6BG = Specific Device Code

M = Date Code■ Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBF4416A	SOT-23 (Pb-Free/ Halide Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MMBF4416A

THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted.})$ (Note 3)

Symbol	Parameter	Max	Unit
P_{D}	Total Device Dissipation Derate above 25°C	225 1.8	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	556	°C/W

^{3.} Device mounted on FR–4 PCB 1.6" \times 1.6" \times 0.06".

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit		
OFF CHARACTERISTICS								
V _{(BR)GSS}	Gate-Source Breakdown Voltage	V _{DS} = 0, I _G = 1.0 μA	-35	-	-	V		
I _{GSS}	Gate Reverse Current	$V_{GS} = -20 \text{ V}, V_{DS} = 0$	-	-	-100	pА		
V _{GS} (off)	Gate-Source Cut-off Voltage	V _{DS} = 15 V, I _D = 1.0 nA	-2.5	-	-6.0	V		
V_{GS}	Gate-Source Voltage	$V_{DS} = 15 \text{ V}, I_D = 500 \mu\text{A}$	-1.0	-	-5.5	V		
ON CHARA	ON CHARACTERISTICS							
I _{DSS}	Zero-Gate Voltage Drain Current	V _{GS} = 15 V, V _{GS} = 0	5	-	15	mA		
V _{GS} (f)	Gate-Source Forward Voltage	$V_{DS} = 0$, $I_{G} = 1.0 \text{ mA}$	-	-	1	V		
SMALL SIG	NAL CHARACTERISTICS							
9 _{fs}	Forward Transfer Admittance (Note 4)	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1.0 \text{ kHz}$	4500	-	7500	μmhos		
gos	Output Admittance (Note 4)	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1.0 \text{ kHz}$	-	-	50	μmhos		
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1.0 \text{ MHz}$	-	-	4.0	pF		
C _{rss}	Reverse Transfer Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1.0 \text{ MHz}$	-	-	0.8	pF		
C _{oss}	Output Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1.0 \text{ MHz}$	-	_	2.0	pF		
NF	Noise Figure	V_{DS} = 15 V, V_{GS} = 0, I_D = 5 mA, R_g = 1 k Ω , f = 400 MHz	-	_	4.0	dB		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse test: pulse width ≤ 300 ms, duty cycle ≤ 2%

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